

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	4.5	A
Peak Pulse Current	I <sub>CM</sub>	10	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

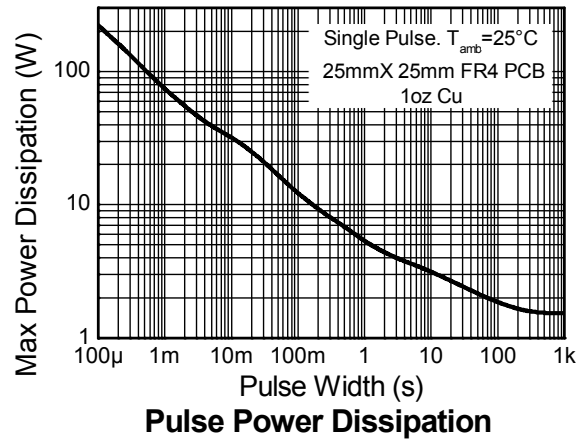
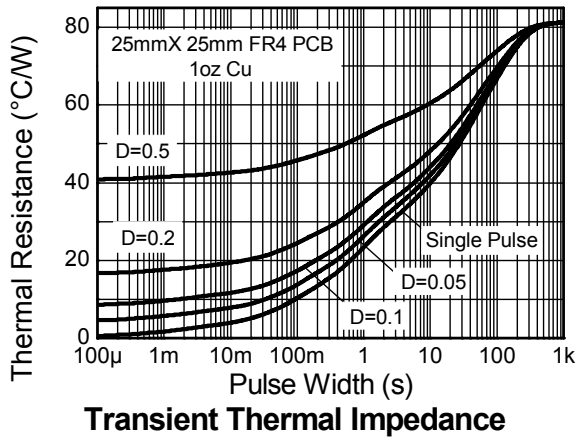
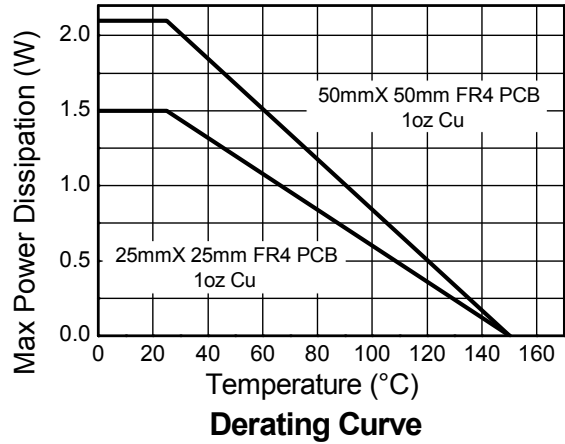
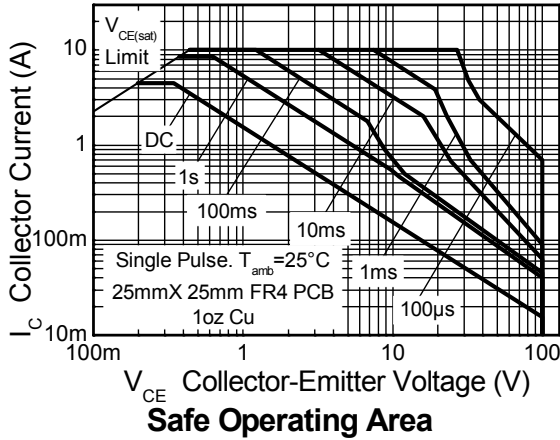
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	1.5	W
Linear derating factor		12	mW/°C
Power Dissipation (Note 6)	P <sub>D</sub>	2.1	W
Linear derating factor		16.8	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	83	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	60	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJL</sub>	3.23	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.
  - Same as note (5), except the device is mounted on 50mm X 50mm single sided 1oz weight copper.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

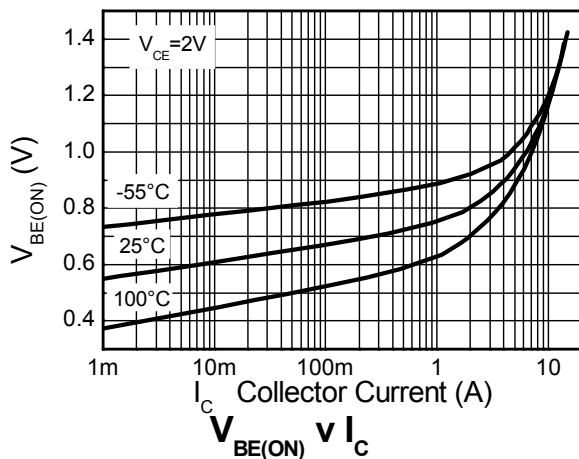
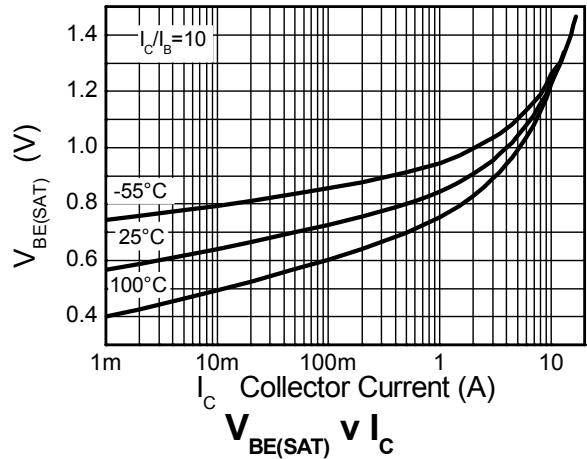
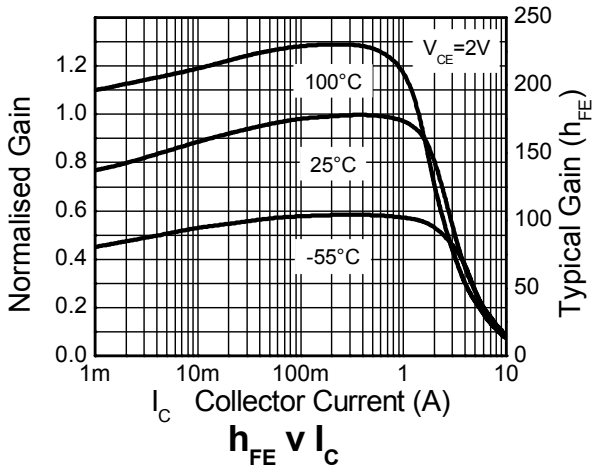
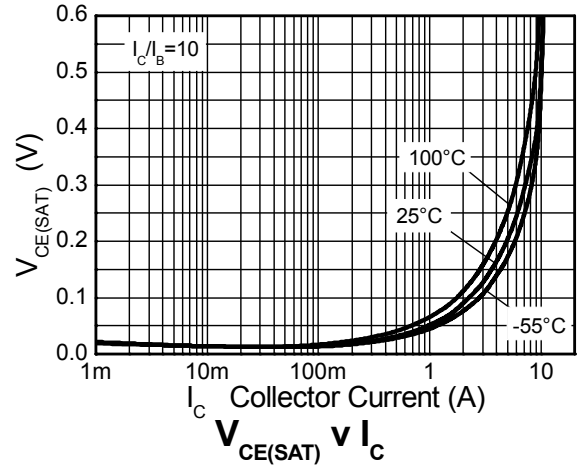
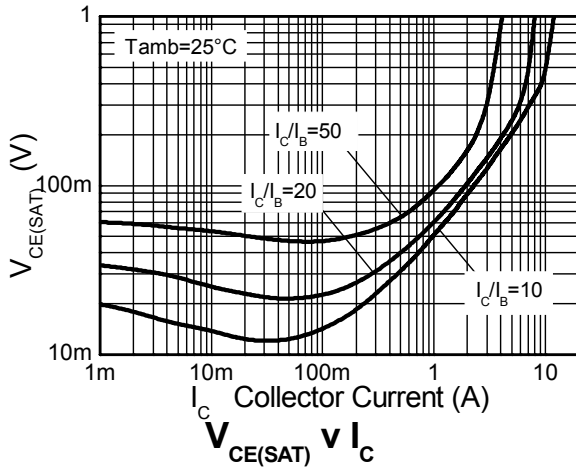


**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	200	235	-	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Notes 9)	$BV_{CER}$	200	235	-	V	$I_C = 1\mu\text{A}$ , $R_B \leq 1\text{k}\Omega$
Collector-Emitter Breakdown Voltage (Notes 9)	$BV_{CEO}$	100	115	-	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7	8.1	-	V	$I_E = 100\mu\text{A}$
Collector Cutoff Current	$I_{CBO}$	-	<1	50	nA	$V_{CB} = 150\text{V}$
		-	-	500	nA	$V_{CB} = 150\text{V}$ , $T_A = +100^\circ\text{C}$
Collector Cutoff Current	$I_{CER}$	-	<1	100	nA	$V_{CB} = 150\text{V}$
	$R \leq 1\text{k}\Omega$	-	-	500	nA	$V_{CB} = 150\text{V}$ , $T_A = +100^\circ\text{C}$
Emitter Cutoff Current	$I_{EBO}$	-	<1	10	nA	$V_{EB} = 6\text{V}$
DC Current Transfer Static Ratio (Notes 9)	$h_{FE}$	100	230	-	-	$I_C = 10\text{mA}$ , $V_{CE} = 2\text{V}$
		100	200	300		$I_C = 2\text{A}$ , $V_{CE} = 2\text{V}$
		30	60	-		$I_C = 5\text{A}$ , $V_{CE} = 2\text{V}$
		10	20	-		$I_C = 10\text{A}$ , $V_{CE} = 2\text{V}$
Collector-Emitter Saturation Voltage (Notes 9)	$V_{CE(sat)}$	-	20	30	mV	$I_C = 100\text{mA}$ , $I_B = 5\text{mA}$
		-	45	60		$I_C = 1\text{A}$ , $I_B = 100\text{mA}$
		-	85	115		$I_C = 2\text{A}$ , $I_B = 100\text{mA}$
		-	155	195		$I_C = 5\text{A}$ , $I_B = 500\text{mA}$
Base-Emitter Saturation Voltage (Notes 9)	$V_{BE(sat)}$	-	1000	1100	mV	$I_C = 5\text{A}$ , $I_B = 500\text{mA}$
Base-Emitter Turn-on Voltage (Notes 9)	$V_{BE(on)}$	-	900	1000	mV	$I_C = 5\text{A}$ , $V_{CE} = 2\text{V}$
Transitional Frequency	$f_T$	-	130	-	MHz	$I_C = 100\text{mA}$ , $V_{CE} = 10\text{V}$ , $f = 50\text{MHz}$
Output Capacitance	$C_{obo}$	-	26	-	pF	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}$ ,
Switching Time	$t_{on}$	-	41	-	ns	$V_{CC} = 10\text{V}$ , $I_C = 1\text{A}$ , $I_{B1} = I_{B2} = 100\text{mA}$
	$t_{off}$	-	1010	-		

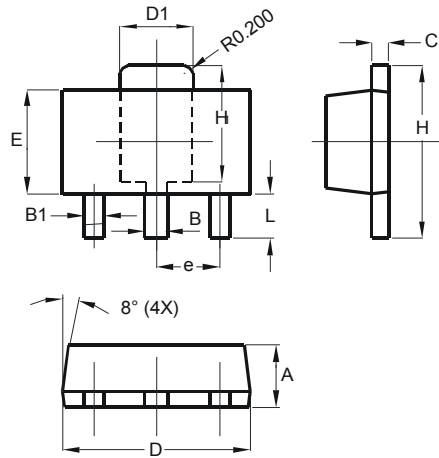
Notes: 8. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



## Package Outline Dimensions

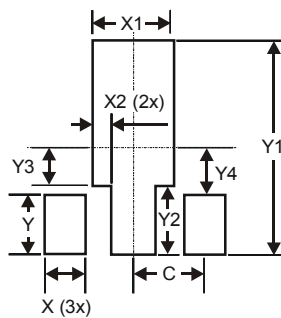
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions in mm		

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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